a light scattering body formed over a second surface of the substrate which is opposite to the first surface.

38 (New). A self-light emitting device according to claim 37, wherein the first electrode is electrically connected to a thin film transistor.

39 (New). A self-light emitting device according to claim 37, wherein the first electrode is an anode, and the second electrode is a cathode.

40 (New). A self-light emitting device according to claim 37, wherein the first electrode comprises a transparent material, and the second electrode comprises a light shielding material.

41 (New). A self-light emitting device according to claim 37, wherein the light scattering body comprises a transparent material.

42 (New). A self-light emitting device according to claim 37, wherein the light scattering body comprises one selected from the group consisting of polycarbonate, polyimide, BCB, indium oxide, and tin oxide.

43 (New). A self-light emitting device according to claim 37, wherein a thickness (H) of the light scattering body has a relation of H W1 with respect to a pitch (W1) of the light scattering body.

44 (New). A self-light emitting device according to claim 37, wherein a pixel pitch is at least twice as long as a pitch of the light scattering body.

45 (New). A self-light emitting device according to claim 37, wherein an angle between the light scattering body and the second surface is not less than 60° and is less than 180°

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46 (New). A self-light emitting device according to claim 37, wherein the self-light emitting device is incorporated into one of selected from the group consisting of an EL display, a video camera, and a computer.

47 (New). A self-light emitting device comprising:

a substrate;

a first electrode formed over a first surface of the substrate;

an EL layer formed on the first rectione

a second electrode formed on the EL layer; and

a light scattering body formed over a second surface of the substrate which is opposite to the first surface,

wherein a thickness (H) of the light scattering body has a relation of H ³ W1 with respect to a pitch (W) of the light scattering body.

48 (New). A self-light emitting device according to claim 47, wherein the first electrode is electrically connected to a thin film transistor.

49 (New). A self-light emitting device according to claim 47, wherein the first electrode is an anode, and the second electrode is a cathode.

50 (New). A self-light emitting device according to claim 47, wherein the first electrode comprises a transparent material, and the second electrode comprises a light shielding material.

51 (New). A self-light emitting device according to claim 47, wherein the light scattering body comprises a transparent material.

52 (New). A self-light emitting device according to claim 47, wherein the light scattering body comprises one selected from the group consisting of polycarbonate, polyimide, BCB, indium oxide, and tin oxide.

53 (New). A self-light emitting device according to claim 47, wherein a pixel pitch is at least twice as long as a pitch of the light scattering body.

54 (New). A self-light emitting device according to claim 47, wherein an angle between the light scattering body and the second surface is not less than 60° and is less than 180°

55 (New). A self-light emitting device according to claim 47, wherein the self-light emitting device is incorporated into one of selected from the group consisting of an EL display, a video camera, and a computer.

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56 (New). A self-light emitting device comprising:

a substrate;

a first electrode formed over a first surface of the substrate;

an EL layer formed on the first electrode;

a second electrode formed on the EL layer; and

a light scattering body formed over a second surface of the substrate which is opposite

to the first surface,

wherein an angle between the light scattering body and the second surface is not less than 60° and is less than 180°.

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57 (New). A self-light emitting device according to claim 56, wherein the first electrode is electrically connected to a thin film transistor.

58 (New). A self-light emitting device according to claim 56, wherein the first electrode is an anode, and the second electrode is a cathode.

59 (New). A self-light emitting device according to claim 56, wherein the first electrode comprises a transparent material, and the second electrode comprises a light shielding material.

60 (New). A self-light emitting device according to claim 56, wherein the light scattering body comprises a transparent material.

61 (New). A self-light emitting device according to claim 56, wherein the light scattering body comprises one selected from the group consisting of polycarbonate, polyimide, BCB, indium oxide, and tin oxide.

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62 (New). A self-light emitting device according to claim 56, wherein a thickness (H) of the light scattering body has a relation of H ³ W1 with respect to a pitch (W1) of the light scattering body.

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63 (New). A self-light emitting device according to claim 56, wherein a pixel pitch is at least twice as long as a pitch of the light scattering body.

64 (New). A self-light emitting device according to claim 56, wherein the self-light emitting device is incorporated into one of selected from the group consisting of an EL display, a video camera, and a computer.

65 (New). A self-light emitting device comprising;

- a substrate;
- a first electrode formed over a surface of the substrate;
- an EL layer formed on the first electrode;
- a second electrode formed on the EL layer; and
- a light scattering body formed over the second electrode.

66 (New). A self-light emitting device according to claim 65, wherein the first electrode is electrically connected to a thin film transistor.

67 (New) . A self-light emitting device according to claim 65, wherein the light scattering body comprises a transparent material.

68 (New). A self-light emitting device according to claim 65, wherein the light scattering body comprises one selected from the group consisting of polycarbonate, polyimide, BCB, indium oxide, and tin oxide.

69 (New). A self-light emitting device according to claim 65, wherein a thickness (H) of the light scattering body has a relation of H ³ (W) with respect to a pitch (W1) of the light scattering body.

70 (New). A self-light emitting device according to claim 65, wherein a pixel pitch is at least twice as long as a pitch of the light scattering body.

71 (New). A self-light emitting device according to claim 65, wherein an angle between the light scattering body and the surface is not less than 60° and is less than 180°

72 (New). A self-light emitting device according to claim 65, wherein the self-light emitting